

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Priority Application Serial No. 09/905,210
Priority Filing Date July 13, 2001
Inventor Cem Basceri et al.
Assignee Micron Technology, Inc.
Priority Group Art Unit 1762
Priority Examiner Eric B. Fuller
Attorney Docket No. MI22-2501
Customer No. 021567
Title: Chemical Vapor Deposition Methods of Forming a Barium Strontium Titanate Comprising Dielectric Layer Having a Varied Concentration of Barium and Strontium With the Layer

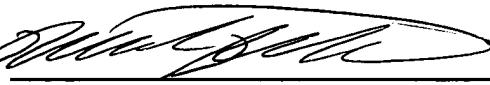
INFORMATION DISCLOSURE STATEMENT

References -- See Attached Form PTO-1449

The attached form PTO-1449 is submitted in compliance with 37 CFR §1.56. Pursuant to 1276 OG 55, August 5, 2003, no copies of cited U.S. patents or U.S. patent application publications are included, as the date of filing of this patent application occurs after June 30, 2003. No admission is made regarding whether all the listed references are prior art.

Respectfully submitted,

Dated: 1-30-04

By: 
Mark S. Matkin
Reg. No. 32,268

Form PTO-1449		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. MI22-2501	PRIORITY SERIAL NO. 09/905,320
LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)		APPLICANT: Cem Basceri et al.			
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